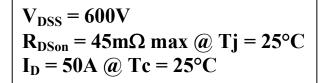
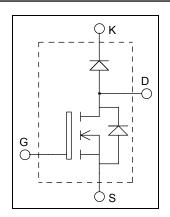


# ISOTOP® Boost chopper Super Junction MOSFET Power Module





### **Application**

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction
- Brake switch

#### **Features**



- Ultra low R<sub>DSon</sub>
- Low Miller capacitance
- Ultra low gate charge
- Avalanche energy rated

#### SiC Schottky Diode

- Zero reverse recovery
- Zero forward recovery
- Temperature Independent switching behavior
- Positive temperature coefficient on VF
- ISOTOP® Package (SOT-227)
- Very low stray inductance
- High level of integration

#### **Benefits**

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- RoHS Compliant

## **Absolute maximum ratings**

Symbol	Parameter		Max ratings	Unit
$V_{ m DSS}$	Drain - Source Breakdown Voltage		600	V
т	( Continuous I )rain ( Current	$T_c = 25^{\circ}C$	50	
$I_{D}$		$T_c = 80^{\circ}C$	38	Α
$I_{DM}$	Pulsed Drain current		130	
$V_{GS}$	Gate - Source Voltage		±20	V
$R_{DSon}$	Drain - Source ON Resistance		45	mΩ
$P_D$	Maximum Power Dissipation	$T_c = 25^{\circ}C$	290	W
$I_{AR}$	Avalanche current (repetitive and non repetitive)		15	A
$E_{AR}$	Repetitive Avalanche Energy		3	mJ
$E_{AS}$	Single Pulse Avalanche Energy		1900	1113

These Devices are sensitive to Electrostatic Discharge. Proper Handing Procedures Should Be Followed.



## All ratings @ $T_j = 25$ °C unless otherwise specified

### **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 600V$	$T_j = 25^{\circ}C$			250	μА
		$V_{GS} = 0V, V_{DS} = 600V$	$T_j = 125$ °C			500	
R <sub>DS(on)</sub>	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 22.5A$			40	45	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 3mA$		2.1	3	3.9	V
$I_{GSS}$	Gate – Source Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$				100	nA

## **Dynamic Characteristics**

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0V ; V_{DS} = 25$	5V		6.8		nF
$C_{oss}$	Output Capacitance	f = 1MHz			0.32		111
$Q_{g}$	Total gate Charge	$V_{GS} = 10V$			150		
$Q_{gs}$	Gate – Source Charge	$V_{\text{Bus}} = 300 \text{V}$			34		nC
$Q_{\text{gd}}$	Gate – Drain Charge	$I_D = 44A$			51		
$T_{d(on)}$	Turn-on Delay Time	Tj=25°C			30		
$T_{\rm r}$	Rise Time	$V_{GS} = 10V$			20		
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 400V$ $I_{\text{D}} = 44A$			100		ns
$T_{\mathrm{f}}$	Fall Time	$R_G = 3.3\Omega$			20		
Eon	Turn-on Switching Energy	$Tj=25^{\circ}C$ $V_{GS} = 10V ; V_{Bus} = 400V$			405		1
E <sub>off</sub>	Turn-off Switching Energy	$I_D = 44A$ ; $R_G = 3.30$			520		μJ
$E_{on}$	Turn-on Switching Energy	$Tj=125^{\circ}C$ $V_{GS} = 10V$ ; $V_{Bus} = 400V$ $I_D = 44A$ ; $R_G = 3.3\Omega$			660		T
$E_{\text{off}}$	Turn-off Switching Energy				635		μJ
$V_{\mathrm{SD}}$	Diode Forward Voltage	$V_{GS} = 0V, I_S = -44A$	1		0.9	1.2	V
$t_{rr}$	Reverse Recovery Time	$I_S = -44A$	$T_j = 25^{\circ}C$		600		ns
$Q_{rr}$	Reverse Recovery Charge	$V_R = 400V$ $di_S/dt = 100A/\mu s$	$T_j = 25^{\circ}C$		17		μС

## SiC chopper diode ratings and characteristics

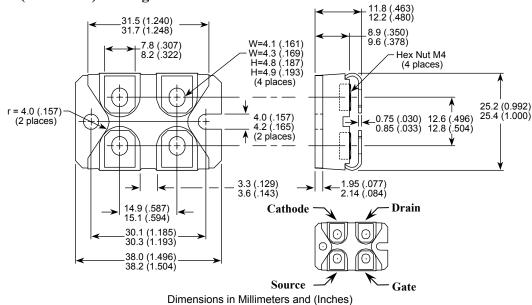
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage			600			V
$I_{RM}$	Maximum Reverse Leakage Current	V <sub>R</sub> =600V	$T_j = 25^{\circ}C$ $T_i = 175^{\circ}C$		100 200	400 2000	μА
$I_{F(AV)}$	Maximum Average Forward Current	50% duty cycle	Tc = 125°C		20		A
<b>V</b> /	Diode Forward Voltage	$I_F = 20A$	$T_j = 25^{\circ}C$		1.6	1.8	V
$V_{\mathrm{F}}$			$T_j = 175$ °C		2	2.4	
Qc	Total Capacitive Charge	$I_F = 20A, V_R = 300V$ di/dt = $800A/\mu s$			28		nC
Q	T. I.G.	$f = 1 MHz, V_R = 200V$			130		
	Total Capacitance	$f = 1MHz, V_R =$	= 400V		100		pF



### Thermal and package characteristics

Symbol	Characteristic		Min	Тур	Max	Unit
$R_{\text{thJC}}$	Junction to Case Thermal Resistance	CoolMos			0.43	°C/W
		SiC Diode			1.4	
$R_{thJA}$	Junction to Ambient (IGBT & Diode)				20	
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t = 1 min, I isol<1mA, 50/60Hz		2500			V
$T_J, T_{STG}$	Storage Temperature Range		-40		150	°C
$T_{ m L}$	Max Lead Temp for Soldering:0.063" from case for 10 sec				300	C
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)				1.5	N.m
Wt	Package Weight			29.2		g

## **SOT-227 (ISOTOP®) Package Outline**



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